

Supporting Information

Dipole Tuning of Charge Transport in Molecular Junctions

Rupa K. Hiremath, Mohammad Hussain K. Rabinal* and Basavaraj G. Mulimani

Departments of Physics, Karnatak University, Dharwad 580003, India

***e-mail - mkrabinal@yahoo.com**

Highly doped (p^+) Si surfaces were modified with molecules belonging to ethynylbenzene series. The molecules are attached covalently to the silicon surface by thermo-chemical reaction. X-ray photoelectron spectroscopic measurements are done for the modified surfaces using ESCLAB spectrometer at a take-off angle 35° and pressure of 10^{-11} torr. The spectra for p^+ -Si surfaces modified with EBZ and DEBZ molecules are shown below. It showed Si (2p) peak at 99.8 eV and C-peak around 285 eV indicating molecular bonding to Si surface. There was no presence of oxygen or any other contamination.

